

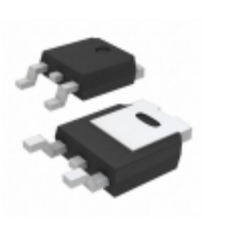




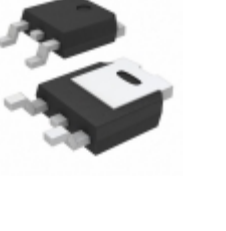


 life.augmented	Hersteller-Teilenummer: STD11N50M2
	Hersteller / Marke: STMicroelectronics
	Teil der Beschreibung: MOSFET N-CH 500V 8A DPAK
	Datenblätter:  STD11N50M2.pdf
RoHs Status: Bleifrei / RoHS-konform	Lagerzustand: New original, 9299 pcs Stock Available.
Lieferung von: Hong Kong	Versandweg: DHL/Fedex/TNT/UPS/EMS
Image may be representation. See specs for product details.	

Spezifikationen

Teilenummer	STD11N50M2
Hersteller	STMicroelectronics
Beschreibung	MOSFET N-CH 500V 8A DPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	9299 pcs Stock
Serie	MDmesh™ II Plus
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Supplier Device-Gehäuse	DPAK
Verlustleistung (max)	85W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	500V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	8A (Tc)
Rds On (Max) @ Id, Vgs	530 mOhm @ 4A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	12nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	395pF @ 100V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±25V
Verpackung	Tape & Reel (TR)



















































STD11N50M2 ist neu im Original, Suche STD11N50M2 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie STD11N50M2 STMicroelectronics mit Garantie und Vertrauen.
Anfrage STD11N50M2: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>STD11N65M5 STMicroelectronics MOSFET N CH 650V 9A DPAK</p>	 <p>STD116GK14B Sirectifier IGBT Modules</p>	 <p>STD116GK16 Sirectifier IGBT Modules</p>	 <p>STD11N60DM2 STMicroelectronics N-CHANNEL 600 V, 0.26 OHM TYP.,</p>
 <p>STD116GK18 Sirectifier IGBT Modules</p>	 <p>STD11N65M2 STMicroelectronics MOSFET N-CH 650V 7A DPAK</p>	 <p>STD116GK18B Sirectifier IGBT Modules</p>	 <p>STD116GK16B Sirectifier IGBT Modules</p>

heiße Teile

Mehr

 STD10NF10T4	 STD10NF30	 STD10NF30	 STD10NM50N	 STD10NM60N
 STD10NM60ND	 STD10NM65N	 STD10P10F6	 STD10P6F6	 STD10PF06
 STD10PF06-1	 STD10PF06L	 STD10PF06T4	 STD110N8F6	 STD110NH02LT4
 STD116GK08	 STD116GK08B	 STD116GK12	 STD116GK12B	 STD116GK14
 STD116GK14B	 STD116GK16	 STD116GK16B	 STD116GK18	 STD116GK18B
 STD11N65M2	 STD11N65M5	 STD11NM50N	 STD11NM60N	 STD11NM60ND
 STD120N4F6	 STD120N4LF6	 STD123SF	 STD123UF	 STD125GK16
 STD12L01	 STD12L01A	 STD12N05LT4	 STD12N06	 STD12N06L
 STD12N06LT4	 STD12N06T4	 STD12N10L	 STD12N10L-TR	 STD12N50M2
 STD12N60M2	 STD12N65M5	 STD12NE06	 STD12NE06L-TR	 STD12NE06LT4

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